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•	Dedicated PWM Input Port Optimized for Reversible Operation of		DWP PACKAGE (TOP VIEW)					
	Motors	GNDS [	1	20 GNDS				
•	Two Input Control Lines for Reduced Microcontroller Overhead	V <sub>CC</sub> [ DIR [	2	19 V <sub>CC</sub> 18 STATUS2				
•	Internal Current Shutdown of 5 A	V <sub>CC</sub> [	4	17 V <sub>CC</sub>				
•	40 V Load Dump Rating	Э Э	5	16 OUT2				
•	Integrated Fault Protection and Diagnostics	99	6	15 OUT2				
•	CMOS Compatible Schmitt Trigger Inputs	GND [] PWM [	<i>7</i> 8	14   GND 13   STATUS1				
	for High Noise Immunity	3	9	12 GND				
_		GNDS ∏	10	11 GNDS				

#### description

The TPIC0107B is a PWM control intelligent H-bridge designed specifically for dc motor applications. The device provides forward, reverse, and brake modes of operation. A logic supply voltage of 5 V is internally derived from  $V_{CC}$ .

The TPIC0107B has an extremely low  $r_{DS(on)}$ , 280 m $\Omega$  typical, to minimize system power dissipation. The direction control (DIR) and PWM control (PWM) inputs greatly simplify the microcontroller overhead requirement. The PWM input can be driven from a dedicated PWM port while the DIR input is driven as a simple low speed toggle.

The TPIC0107B provides protection against over-voltage, over-current, over-temperature, and cross conduction faults. Fault diagnostics can be obtained by monitoring the STATUS1 and STATUS2 terminals and the two input control lines. STATUS1 is an open-drain output suitable for wired-or connection. STATUS2 is a push-pull output that provides a latched status output. Under-voltage protection ensures that the outputs, OUT1 and OUT2, will be disabled when  $V_{CC}$  is less than the under-voltage detection voltage  $V_{(UVCC)}$ .

The TPIC0107B is designed using TI's LinBiCMOS™ process. LinBiCMOS allows the integration of low power CMOS structures, precision bipolar cells, and low impedance DMOS transistors.

The TPIC0107B is offered in a 20-pin thermally enhanced small-outline package (DWP) and is characterized for operation over the operating case temperature of –40°C to 125°C.

#### **FUNCTION TABLE**

DIR PWM OUT1		OUT1	OUT2	MODE
0 0 HS		HS	HS	Brake, both HSDs turned on hard
0	1 HS LS		LS	Motor turns counter clockwise
1	1 0 HS		HS	Brake, both HSDs turned on hard
1	1	LS	HS	Motor turns clockwise

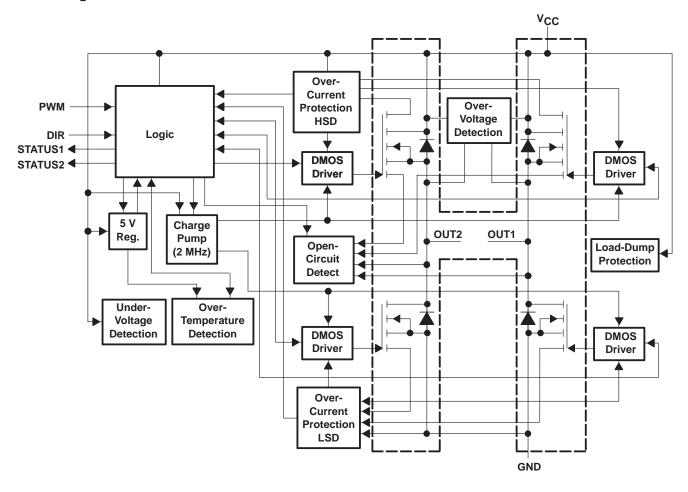


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#### block diagram



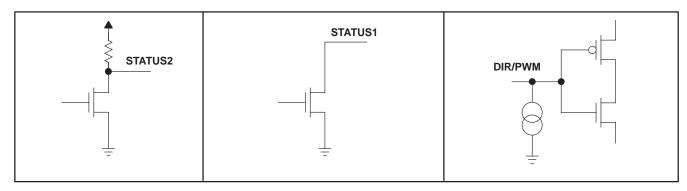
### **Terminal Functions**

TERM	IINAL						
NAME	NO.	1/0	DESCRIPTION				
DIR	3	1	Direction control input				
GND	7, 9, 12, 14	I	Power ground				
GNDS	1, 10, 11, 20	I	Substrate ground				
OUT1	5, 6	0	Half-H output. DMOS output				
OUT2	15, 16	0	Half-H output. DMOS output				
PWM	8	I	PWM control input				
STATUS1	13	0	Status output				
STATUS2	18	0	Latched status output				
VCC	2, 4, 17, 19	I	Supply voltage				

NOTE: It is mandatory that all four ground terminals plus at least one substrate terminal are connected to the system ground. Use all V<sub>CC</sub> and OUT terminals.



## schematics of inputs and outputs



## absolute maximum ratings over operating case temperature range (unless otherwise noted)<sup>†</sup>

Power supply voltage range, V <sub>CC</sub>	0.3 V to 33 V
Logic input voltage range, V <sub>IN</sub>	–0.3 V to 7 V
Load dump (for 400 ms, T <sub>C</sub> = 25°C)	40 V
Status output voltage range, $V_{O(status)}$	–0.3 V to 7 V
Continuous power dissipation, $T_C = 25^{\circ}C$	1.29 W
Storage temperature range, T <sub>stq</sub>	–55°C to 150°C
Maximum junction temperature, T <sub>J</sub>	150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### **DISSIPATION RATING TABLE**

$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR	T <sub>A</sub> = 70°C	T <sub>A</sub> = 125°C
	ABOVE T <sub>A</sub> = 25°C	POWER RATING	POWER RATING
1.29 W	0.0104 W/°C	0.82 W	0.25 W

## recommended operating conditions

	MIN	MAX	UNIT
Supply voltage, V <sub>CC</sub>	6	18	V
Operating case temperature, T <sub>C</sub>	-40	125	°C
Switching frequency, fpWM		2	kHz

# TPIC0107B PWM CONTROL INTELLIGENT H-BRIDGE

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## electrical characteristics over recommended operating case temperature range and $V_{CC} = 5 \text{ V}$ to 6 V (unless otherwise noted)

PARAMETER			TEST CONDITIONS	MIN	TYP	MAX	UNIT
			T <sub>J</sub> = 25°C	5		550	0
	Static drain-source on-resistance (per transistor)	LSD	T <sub>J</sub> = 150°C			850	mΩ
rDS(on)	$I_{(BR)} = 1 A$	HSD	T <sub>J</sub> = 25°C			600	0
		T <sub>J</sub> = 150°C			870	mΩ	
I <sub>(QCD)</sub> Open circuit detection current			10	40	100	mA	
V(UVCC(OFF))	V(UVCC(OFF))       Under voltage detection on VCC, switch off voltage       Set         V(UVCC(ON))       Under voltage detection on VCC, switch on voltage       Set		See Note 1			5	V
V(UVCC(ON))			See Note 1			5.2	V
V(STL)			$I_O = 100 \mu\text{A}$ , See Note 1			0.8	V
V(ST2H)	STATUS2 high output voltage		$I_O = 20 \mu A$ , See Note 1	3		5.4	V
I(ST(OFF))	STATUS output leakage current		V <sub>(ST)</sub> = 5 V, See Note 1			5	μΑ
V <sub>IL</sub>	Low level logic input voltage			-0.3		0.5	V
VIH	High level logic input voltage			3.6		7	V
ΔVΙ	Hysteresis of input voltage			0.3		·	V
ΙΗ	High level logic input current		V <sub>IH</sub> = 3.5 V	2	10	50	μΑ

NOTE 1: The device functions according to the function table for  $V_{CC}$  between  $V_{(UVCC)}$  and 5 V (no parameters specified). STATUS outputs are not defined for  $V_{CC}$  less than  $V_{(UVCC)}$ .



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## electrical characteristics over recommended operating case temperature and supply voltage ranges (unless otherwise noted) (see Note 2)

PARAMETER		TEST	MIN	TYP	MAX	UNIT			
			T . 250C	$V_{CC} = 6 \text{ V to } 9 \text{ V}$			380		
		LSD	T <sub>J</sub> = 25°C	V <sub>CC</sub> = 9 V to 18 V		280	340	1	
		LSD	T 4500C	V <sub>CC</sub> = 6 V to 9 V			620	mΩ	
	Static drain-source on-resistance		T <sub>J</sub> = 150°C	V <sub>CC</sub> = 9 V to 18 V		400	560		
rDS(on)	(per transistor) I <sub>BR</sub> = 1 A		T. 25°C	$V_{CC} = 6 V \text{ to } 9 V$			430		
		HSD	T <sub>J</sub> = 25°C	$V_{CC} = 9 V \text{ to } 18 V$		280	340	<b>~</b> 0	
		нэр	T. 4500C	$V_{CC} = 6 \text{ V to } 9 \text{ V}$			640	mΩ	
			T <sub>J</sub> = 150°C	$V_{CC} = 9 V \text{ to } 18 V$		400	560		
I(QCD)	Open circuit detection current				10	40	100	mA	
T <sub>SDS</sub>	Static thermal shutdown temperature	е	See Notes 3 and 4		140			°C	
T <sub>SDD</sub>	Dynamic thermal shutdown tempera	iture	See Notes 3 and 5		160			°C	
	Command about day on limit		V <sub>CC</sub> = 6 V to 9 V		4.8		7.5	Α	
ICS	Current shutdown limit		V <sub>CC</sub> = 9 V to 18 V		5		7.5	А	
I(CON)	Continuous bridge current		T <sub>J</sub> = 125°C, Operating lifetime 10,000 hours, (see Figure 1)				3	Α	
V(OVCC)	Over voltage detection on V <sub>CC</sub>				27		36	V	
V(STL)	STATUS low output voltage		ΙΟ = 100 μΑ				0.8	V	
V <sub>(ST2H)</sub>	STATUS2 high output voltage		I <sub>O</sub> = 20 μA		3.9		5.4	V	
I(ST(OFF))	STATUS output leakage current		$V_{(ST)} = 5 V$				5	μΑ	
$V_{IL}$	Low level logic input voltage				-0.3		0.8	V	
VIH	High level logic input voltage				3.6		7	V	
ΔVΙ	Hysteresis of input voltage				0.3			V	
ΊΗ	High level logic input current		V <sub>IH</sub> = 3.5 V		2	10	50	μΑ	

NOTES: 2. The device functions according to the function table for V<sub>CC</sub> between 18 V and V<sub>(OVCC)</sub>, but only up to a maximum supply voltage of 33 V (no parameters specified). Exposure beyond 18 V for extended periods may affect device reliability.

- 3. Exposure beyond absolute-maximum-rated condition of junction temperature may affect device reliability.
- 4. No temperature gradient between DMOS transistor and temperature sensor.
- 5. With temperature gradient between DMOS transistor and temperature sensor in a typical application (DMOS transistor as heat source).

## switching characteristics over recommended operating case temperature and supply voltage ranges (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
	High-side driver turn-on time	V 4.V 24.4 A V 42.0 V			100	
tout(on)	Low-side driver turn-on time	$V_{DS(on)}$ <1 V at 1 A, $V_{CC}$ = 13.2 V			100	μs
O.D.	Slew rate, low-to-high sinusoidal (δV/δt)	V 40.0 V 1 4 A mariative land	1		6	\// -
SR	Slew rate, high-to-low sinusoidal ( $\delta V/\delta t$ )	$V_{CC} = 13.2 \text{ V},$ $I_{O} = 1 \text{ A resistive load}$	1		6	V/μs
td(QCD)	Under current spike duration to trigger open circuit detection	V <sub>CC</sub> = 5 V to 18 V	1		10	ms
t <sub>d</sub> (CS)	Delay time for over current shutdown		5	10	25	μs

#### thermal resistance

	PARAMETER		MAX	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance		97	°C/W
$R_{\theta JC}$	Junction-to-case thermal resistance		5	°C/W



## PARAMETER MEASUREMENT INFORMATION

Maximum continuous bridge current versus time based on 50 FITs at 100,000 hours operating life (90% confidence model)

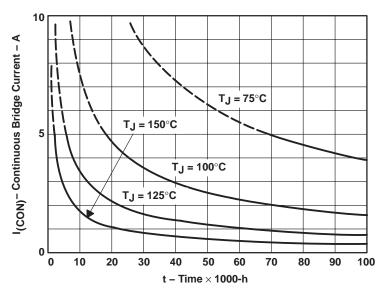


Figure 1. Electromigration Reliability Data

#### Example:

Average continuous bridge current, ICON		Average junction temperature, T <sub>J</sub>	Operating lifetime of device based on electromigration				
	2 A	125°C	>20,000 h				
	3 A	125°C	>10,000 h				



## PARAMETER MEASUREMENT INFORMATION

## operating wave forms

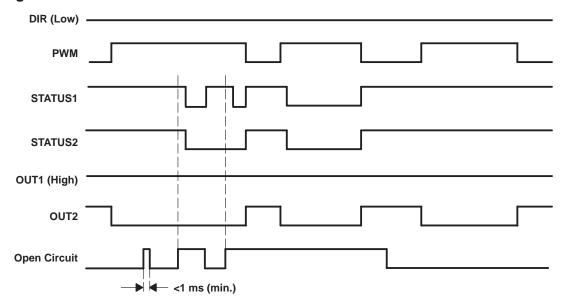


Figure 2. Open Circuit

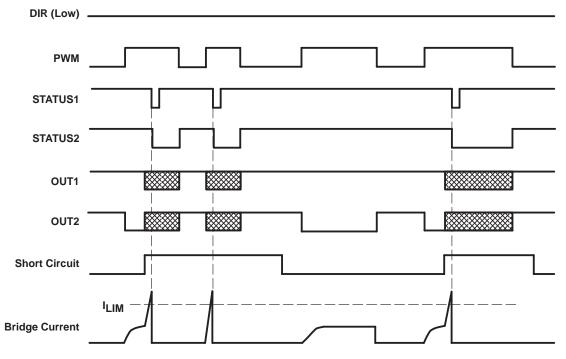


Figure 3. Short Circuit (e.g., OUT2 to V<sub>CC</sub>)

**Brake** 

#### PARAMETER MEASUREMENT INFORMATION

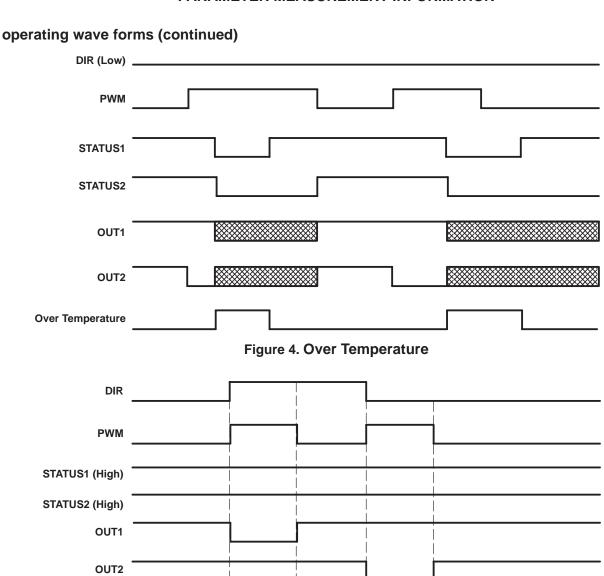


Figure 5. No Fault

**Brake** 

Counter-

Clockwise Rotation

Clockwise

Rotation

**Brake** 



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#### PRINCIPLES OF OPERATION

### protective functions and diagnostics<sup>†</sup>

#### over current/short circuit‡

The TPIC0107B detects shorts to  $V_{CC}$ , ground, or across the load being driven, by comparing the  $V_{DS}$  voltage drop across the DMOS outputs against the threshold voltage. The DMOS outputs of the TPIC0107B will be disabled and the fault flags will be generated 10  $\mu$ s after an over-current or short-circuit fault is detected. This 10  $\mu$ s delay is long enough to serve as a de-glitch filter for high current transients, yet short enough to prevent damage to the DMOS outputs. The DMOS outputs remain latched off until either DIR or PWM input is toggled.

In cases where the outputs have a continuous short-to-ground with a current rise time faster than 0.5 A/ $\mu$ s, the over-current shutdown threshold will decrease to 3 A to reduce power dissipation. This reduction to 3 A is achieved since the DMOS outputs will not be fully enhanced when the over-current threshold is reached if the current rise time exceeds 0.5 A/ $\mu$ s. Over-current and/or short-circuit protection is provided up to V<sub>CC</sub> = 16.5 V and a junction temperature of 90°C.

#### over temperature

The TPIC0107B disables all DMOS outputs and the fault flags will be set when  $T_J \ge 140^{\circ}$ C (min.). The DMOS outputs remain latched off until either DIR or PWM input is toggled.

#### under voltage

The TPIC0107B disables all DMOS outputs when  $V_{CC} \leq V_{(UVCC)}$ . The outputs will be re-enabled when  $V_{CC} \geq V_{(UVCC)}$ . No fault flags are set when under-voltage lockout occurs.

#### over voltage

In order to protect the DMOS outputs from damage caused by excessive supply voltage, the TPIC0107B disables all outputs when  $V_{CC} \ge V_{(OVCC)}$ . Once  $V_{CC} \le V_{(OVCC)}$ , either DIR or PWM input must be toggled to re-enable the DMOS outputs.

#### cross conduction

Monitoring circuitry for each transistor detects whether the particular transistor is active to prevent the HSD or LSD of the corresponding half H-bridge from conducting.

#### open circuit

During operation, the bridge current is controlled continuously. If the bridge current is >10 mA (min.) for a period >1 ms (min.), the fault flags are set. However, the output transistors will not be disabled.

<sup>‡</sup> If a short circuit occurs (i.e., the over-current detection circuitry is activated) at a supply voltage higher than 16.5 V and a junction temperature higher than 90°C, damage to the device may occur.



<sup>†</sup> All limits mentioned are typical values unless otherwise noted.

#### PRINCIPLES OF OPERATION

#### **DIAGNOSTICS TABLE (see Note 6)**

FLAG	DIR	PWM	OUT1	OUT2	STATUS1 <sup>†</sup>	STATUS2
	0	0	HS	HS	1	1
Normal operation	0	1	HS	LS	1	1
Normal operation	1	0	HS	HS	1	1
	1	1	LS	HS	1	1
	0	0	HS	HS	1	1
Open circuit between OUT1 and OUT2	0	1	HS	LS	0	0
Open circuit between 0011 and 0012	1	0	HS	HS	1	1
	1	1	LS	HS	0	0
Chart aircuit from OUT1 to OUT2 (and Notes 7 and 9)	0	1	Χ	Х	0	0
Short circuit from OUT1 to OUT2 (see Notes 7 and 8)	1	1	Х	Х	0	0
	0	0	Х	Х	0	0
Short circuit from OUT1 to GND (see Notes 7 and 8)	1	0	Х	Χ	0	0
	0	1	Х	Х	0	0
	0	0	Х	Х	0	0
Short circuit from OUT2 to GND (see Notes 7 and 8)	1	0	Х	Χ	0	0
	1	1	X	Х	0	0
Short circuit from OUT1 to V <sub>CC</sub> (see Notes 7 and 8)	1	1	Х	Х	0	0
Short circuit from OUT2 to V <sub>CC</sub> (see Notes 7 and 8)	0	1	Х	Х	0	0
	0	0	Z	Z	0	0
Over temperature	0	1	Z	Z	0	0
Over temperature	1	0	Z	Z	0	0
	1	1	Z	Z	0	0

† When wired with a pull-up resistor

SYMBOL VALUE

0 Logic low
1 Logic high

HS High-side MOSFET conducting LS Low-side MOSFET conducting Z No output transistors conducting

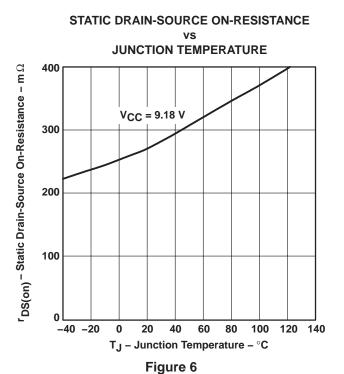
X Voltage level undefined

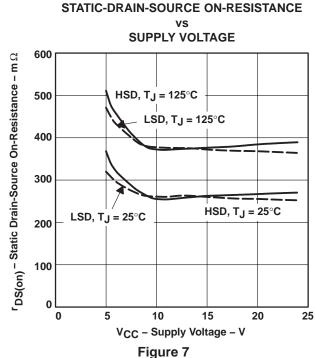
NOTES: 6. All input combinations not stated result in STATUS output = 1.

7. STATUS1 active for a minimum of 3  $\mu$ s. 8. STATUS2 active until an input is toggled.



#### **TYPICAL CHARACTERISTICS**





#### **OUTPUT STAGE TURN-ON TIME**

JUNCTION TEMPERATURE

20

HSD, V<sub>CC</sub> = 13.2 V

LSD, V<sub>CC</sub> = 13.2 V

10

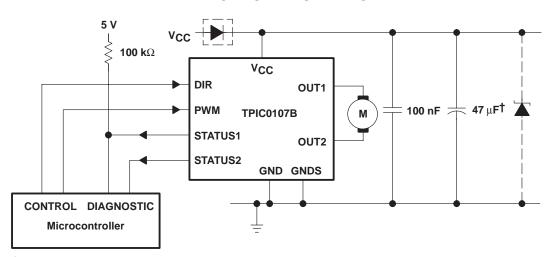
-40 -20 0 20 40 60 80 100 120 140

T<sub>J</sub> - Junction Temperature - °C

Figure 8



#### **APPLICATION INFORMATION**



 $\ensuremath{^{\dagger}}$  Necessary for isolating supply voltage or interruption (e.g., 47  $\mu F).$ 

NOTE: If a STATUS output is not connected to the appropriate microcontroller input, it shall remain unconnected.





com 11-Dec-2008

#### PACKAGING INFORMATION

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins Package Qty	Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
TPIC0107BDWP	OBSOLETE	SO Power PAD	DWP	20	TBD	Call TI	Call TI
TPIC0107BDWPG4	OBSOLETE	SO Power PAD	DWP	20	TBD	Call TI	Call TI
TPIC0107BDWPRG4	OBSOLETE	SO Power PAD	DWP	20	TBD	Call TI	Call TI

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

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Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

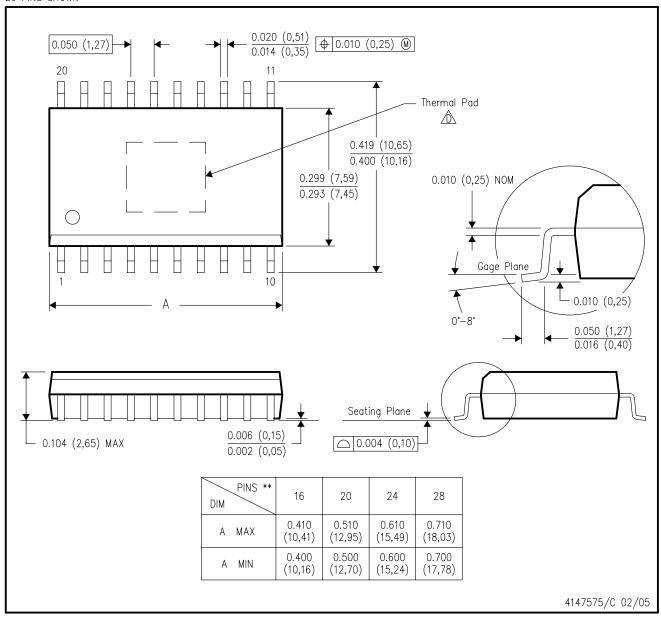
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## DWP (R-PDSO-G\*\*)

## PowerPAD™ PLASTIC SMALL-OUTLINE PACKAGE

20 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <a href="https://www.ti.com">http://www.ti.com</a>. See the product data sheet for details regarding the exposed thermal pad dimensions.

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RF/IF and ZigBee® Solutions	www.ti.com/lprf	Video and Imaging	www.ti.com/video
		Wireless	www.ti.com/wireless-apps